



DMNH6042SPD

60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
60V	50mΩ @ V _{GS} = 10V	24A
00 v	65mΩ @ V _{GS} = 4.5V	21A

This new generation MOSFET is designed to minimize the on-state

resistance R_{DS(ON)} and yet maintain superior switching performance,

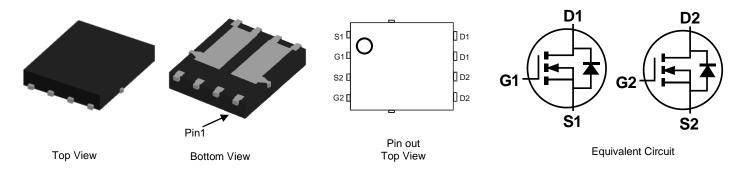
making it ideal for high efficiency power management applications.

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature • Environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low R_{DS(ON)} minimizes power losses
- $Low \; Q_g minimizes \; switching \; losses$
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMNH6042SPDQ)

Mechanical Data

- Case: PowerDI5060-8 (Type C) •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020 •
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Description and Applications

Engine Management Systems

Body Control Electronics

DC-DC Converters

	Part Number	Case	Packaging			
	DMNH6042SPD-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel			
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.						

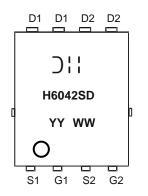
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking H6042SD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016)WW = Week (01 to 53)

DMNH6042SPD Document number: DS37387 Rev. 3 - 2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	60	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	ID	5.7 4.6	А
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T _C = +25°C T _C = +100°C	I _D	24 17	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	32	А
Maximum Continuous Body Diode Forward Current (Note 7)			Is	24	А
Avalanche Current (Note 8) L = 10mH			I _{AS}	3.5	А
Avalanche Energy (Note 8) L = 10mH			E _{AS}	65	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		PD	1.2	W
Thermal Desistance, Junction to Ambient (Note 5)	Steady state	P	105	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ extsf{ heta}JA}$	54	
Total Power Dissipation (Note 6)		PD	2.5	W
Thermal Desistance, Junction to Ambient (Note 6)	Steady state	P	51	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ extsf{ heta}JA}$	26	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	3.5	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

						-
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	60			V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	—		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	3.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	D	_	34	50	mΩ	$V_{GS} = 10V, I_D = 5.1A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	45	65	11122	$V_{GS} = 4.5V, I_D = 4.4A$
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2.6A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	Ciss	—	584	_	pF	
Output Capacitance	Coss	—	83	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	—	24	_	pF	1 = 1.00012
Gate Resistance	Rg	_	3.8		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	4.2		nC	
Total Gate Charge (V _{GS} = 10V)	Qg	—	8.8	_	nC	Vps = 44V. lp = 5.2A
Gate-Source Charge	Q _{gs}	_	1.8	—	nC	$v_{DS} = 44v, I_D = 5.2A$
Gate-Drain Charge	Q _{gd}	_	1.8	_	nC	
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns	
Turn-On Rise Time	t _R	_	1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$
Turn-Off Delay Time	t _{D(OFF)}	_	10.1	—	ns	$R_G = 6\Omega, I_D = 1A$
Turn-Off Fall Time	t _F	_	4.5	_	ns	
Body Diode Reverse Recovery Time	t _{RR}	_	12.9	—	ns	I _F = 2.6A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	_	5.4	—	nC	I _F = 2.6A, di/dt = 100A/µs

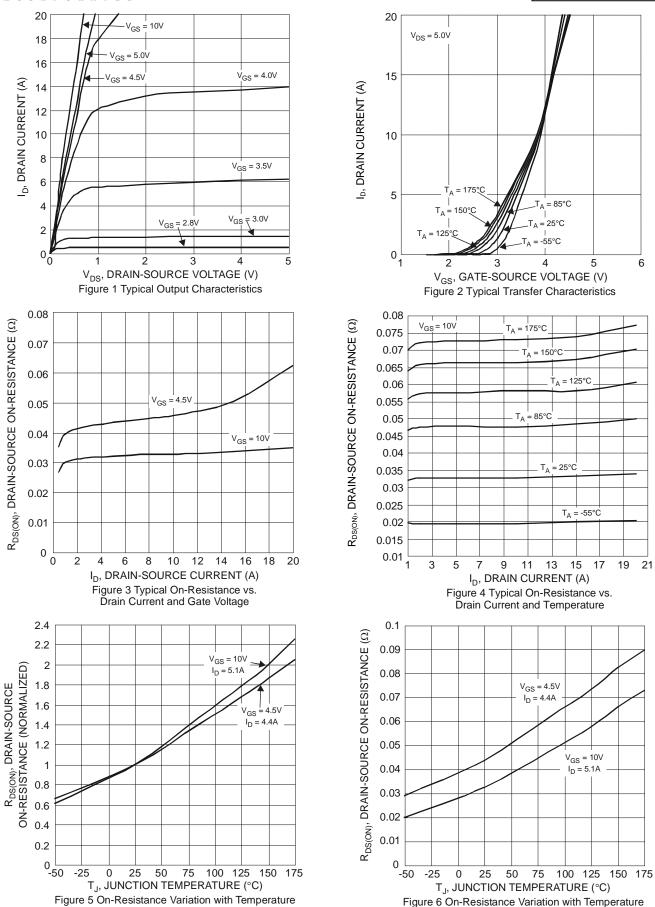
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

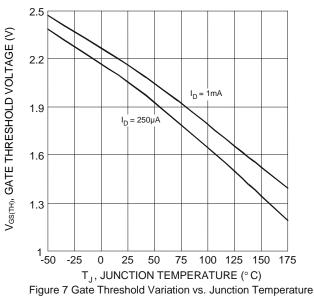
8. Device moduled of PK-4 substate PC board, 202 copper, with iternal blas to bott 7. Thermal resistance from junction to soldering point (on the exposed drain pad). 8. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^{\circ}$ C. 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.

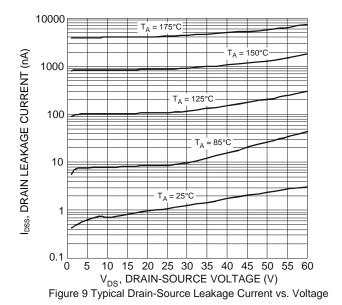


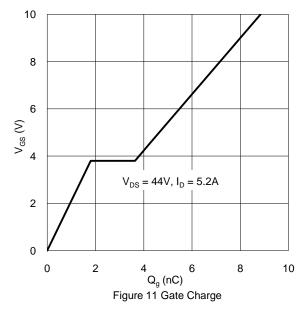












28 26 24 22 20 18 16 14 12 T_A = 175 10 = 85°C T_A = 150°C 8 6 = 25°C TΔ T_A = 85°C 4 = -55°C 2 0 ∟ 0 0.3 0.6 0.9 1.2 1.5 V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current f = 1MHz $\mathbf{C}_{\mathrm{iss}}$ 100 Coss C_{rss} 0 5 10 15 20 25 30 35 40 45 50 55 60 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 10 Typical Junction Capacitance 100 E R_{DS(ON)} Limited 10 1 ΈPw 1s 100n P_W 10ms 0.1 $T_{J(max)} = 150^{\circ}C$ - 1n. +++++ F P_W = 1ms

 P_W

10

V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12 SOA, Safe Operation Area

= 100µs

DMNH6042SPD

30

Is, SOURCE CURRENT (A)

1000

C_T, JUNCTION CAPACITANCE (pF)

DRAIN CURRENT (A)

ó

0.01 0.1

 $T_A = 25^{\circ}C$

V_{GS}= 10V Single Pulse

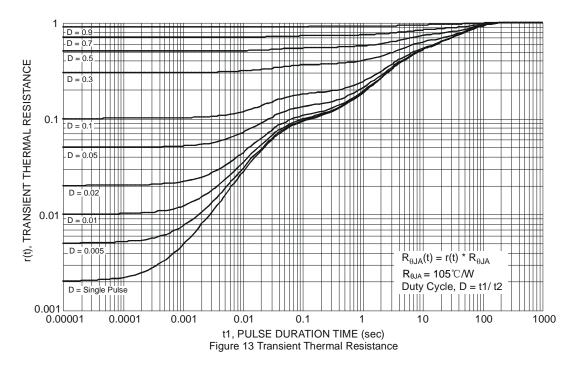
DUT on 1 * MRP Board

10



100



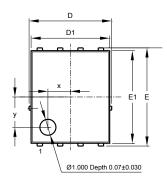


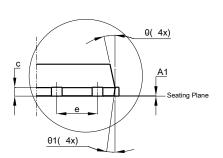


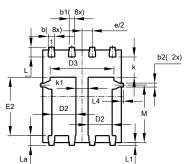
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

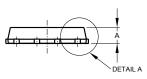
PowerDI5060-8 (Type C)









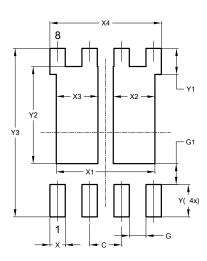


Pow	PowerDI5060-8 (Type C)					
Dim	Min	Тур				
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
С	0.23	0.33	0.277			
D	5	.15 BS0	0			
D1	4.85	4.95	4.90			
D2	1.40	1.60	1.50			
D3	-	3.98				
Е	6	.15 BS0	2			
E1	5.75	5.85	5.80			
E2	3.56	3.76	3.66			
е	1	.27BSC				
k	-	-	1.27			
k1	0.56	-	-			
L	0.51	0.71	0.61			
La	0.51	0.71	0.61			
L1	0.05	0.20	0.175			
L4	-	-	0.125			
М	3.50	3.71	3.605			
х	-	-	1.400			
У	-	-	1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	3.910		
X2	1.650		
X3	1.650		
X4	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated

www.diodes.com